

Final characterization of the ATLAS IBL detector modules with ²⁴¹Am during the construction phase

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The ATLAS Insertable B-Layer (IBL) project

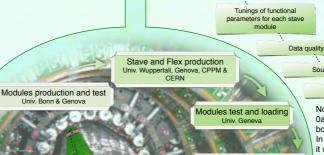
In 2013 during the long shutdown a fourth layer for the ATLAS Pixel detector will be installed at CERN between a new beam pipe (23.5 mm radius) and the current inner Pixel layer (B-Layer at 55

Motivations:

- Pattern recognition robustness in view of higher track multiplicity
- ► Controlling detector occupancy at high luminosity
- Tracking precision for an excellent vertex detector performance
- Large radiation dose will require more radiation hard sensor technology Main requirements:
- Radiation hard technology for sensors and electronics
 Small space available: no shingling and development of sensor with active or slim edge
- Minimize the material in order to have 1.5% of radiation lenght
- Tight tolerances and clearances

Overall Layout:

- Cylindrical layer formed by 14 staves with a length of 72 cm (production of 24 staves)
 Development of new readout chip: FE-I4B (32 FE chips for each stave)
- ► Each stave will host 12 double chip and 8 single chip modules
- Double chip module: Slim Edge Planar Silicon n-in-n design Sensor
 Single chip module: 3D Silicon Sensor
- Total of 12 millions 50 x 250 µm² pixels



IBL Production: final QA

A dedicated set-up has been installed in the SR1 clean room at CERN in order to perform QA tests on the 24 production staves (14 staves to be installed plus 10 spares):

- Thermal insulated aluminium box flushed with dry air
- ► An innovative CO₂ cooling system named TRACI
- Linear stage for automatic source scans over the two staves
- Set-up for stave test with cosmics
- A custom-built DAQ-system based on ATCA with two CIMs (Cluster Interconnect Module) and three RCEs (Reconfigurable Cluster Element).

The loading and QA activities will be performed in different institutes where a precise workflow will be followed during the construction phase

Source scans



Nowadays a first real prototype stave, named Stave Oa, equipped with the foreseen sensor flavours bump bonded to FE-I4A chips has been fully characterized. In the coming months the final QA will be started and it will end in summer 2013.

²⁴¹Am Source Scans for QA

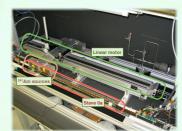
One of the QA activities for the 24 staves that will arrive in SR1 is the performance of source scans in order to see the response of the detector to radiation, identify pixels not answering to ionization and provide data for recalibration of the charge calibration

A dedicated set-up has been implemented in order to perform automated source scans over-all the modules during the production phase:

Two ²⁴¹Am sources of 41 MBq with emission along 11.25 mm each

Linear motor with a special mechanical structure holding the sources over one or two staves moving for the entire stave's length

c++ software for the linear motor communication and for the automation of the source scans along all the stave



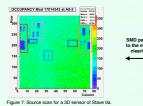
A typical source scan

Source scan for half stave

The ²⁴¹Am source is positioned at a distance of about 4 cm from the module. Given the distance, the source's activity and the chip size, it is possible to calculate that the gamma rate on the chip is of the order of 1 MHz

Several ²⁴¹Am source scans have been performed along all prototype stave with different tuning

parameters. The goal is to have an overall view of the detection properties for each module,



identify the bad pixels and have a charge calibration

A possible charge calibration of all IBL modules

Final production staves QA

In the Fe-I4A IC no circuitry for direct measurement of the test charge injection capacitances has been implemented. Simulations predict a capacitance of 5.7 fF if both injection capacitors are used.

$$N=N_0e^{-\sigma_L x}$$
 $\sigma_L\simeq 2cm^{-1}$ $x=200\mu m$ $\sigma_L\simeq 2cm^{-1}$ $x=200\mu m$ $\sigma_L\simeq 2cm^{-1}$ $\sigma_L\simeq 2cm^{-1}$ $\sigma_L\simeq 2cm^{-1}$ $\sigma_L\simeq 2cm^{-1}$

The absorption of 60 keV photons in Si is dominated by the photoelectric effect even if the Compton scattering is present. Gamma at 60 keV deposits ~ 16.6 ke in the sensor

The position of the photoelectric peak of the measured charge distribution can be used to verify the front-end calibration

The FE-I4 ASIC provides individual pixels charge measurements by means of the Time over Threshold (ToT) method, featuring a 4-bit counter for moderate resolution

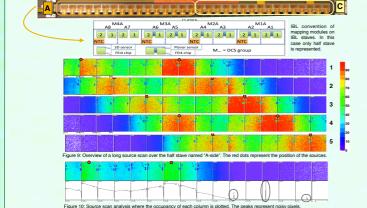


Source scan for bad pixel searching

The 241Am source scan is useful to identify pixels not answering to ionization because disconnected, merged, defective or badly tuned

- · Disconnected bump: bump bond connections can break because of mechanical stress
- Merged bump: still form a connection between sensor and FE, but two or more channels are merged to a single connection





Example of one IBL module on Stave 0a 0 Lego-Plot module A8-2: In the Lego-Plot the bad pixels are plotted as columns with different colours which represent the different types of

A module is accepted for IBL if it shows less than 1% defective pixel

Conclusion

The first stave prototype has been fully characterized in the SR1 clean room at CERN. The systematic quality assurance procedure concerning module, stave and flex from the production to the final assembly on the beampipe has been already started.

A dedicated set-up for automated source scans of the IBL production staves has been implemented. The response of the detector to radiation and the FE charge calibration have been verified by means of ²⁴¹Am source scans. Furthermore a full program for the identification of bad pixel with the help of source scan has been developed.